2023 International Conference on IC Design and Technology (ICICDT 2023)

Tokyo, Japan
25-28 September 2023

IEEE

IEEE Catalog Number: CFP23412-POD
ISBN: 979-8-3503-1932-3

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IEEE Catalog Number:	CFP23412-POD
ISBN (Print-On-Demand):	979-8-3503-1932-3
ISBN (Online):	979-8-3503-1931-6
ISSN:	2381-3555

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Table of Contents

The 2023 International Conference on IC Design and Technology

Table of Contents ii

Conference Committee vii

Technical Program Committee viii

Keynotes

Semiconductor Packaging Revolution in the Era of Chiplets ix
Yasumitsu Orii

Efficient integrated devices are growing on Engineered Substrates x
Christophe Maleville

Embracing the new era of AI at the edge xi
Vincent Huard

Silicon technologies for quantum computing xii
Takahiro Mori

Physical reservoir computing toward edge AI hardware xiii
Ryosho Nakane

Necessary but non-core laboratory analytical works drives semiconductor industry into a new norm: Lableess solution xiv
Xiaomin Li

Invited Talks

Reservoir computing utilizing ferroelectric-gate-insulator FETs and capacitors xv
Shinichi Takagi

Analog Computation-in-Memory (CiM) for AI Applications xvi
Ken Takeuchi

Memristor Based Mixed-Precision Computation-in-Memory System xvii
Bin Gao

Beyond Integer Quantization: Approximate Arithmetic for Machine Learning Accelerators xviii
James Tandon

Challenges in generating true random numbers considering the variety of corners, aging, and attacks xix
Sylvain Guilley

Hafnia-based Ferroelectric Memory: Device Physics Strongly Correlated with Materials Chemistry xx

Min Hyuk Park

BEOL-compatible Oxide Semiconductor Devices _____ xxi
Han Kaizhen

Millimeter-Wave Dual-Frequency Transformer-based Rectifier _____ xxii
Yun Fang

Low-power MEMS-based CMOS Transceivers _____ xxiii
Kai Tang

Towards Ultra-fast Time-based Electrochemical Impedance Spectroscopy of Sensors _____ xxiv
Antonio Radogna

Enabling Quantum Imaging applications with CMOS SPAD arrays _____ xxv
Leonardo Gasperini

Cryogenic InGaAs HEMTs for LNA and routing circuits in Quantum Computing _____ xxvi
Sanghyeon Kim

Investigation of Low Temperature Noise and Current Fluctuation for Advanced Transistors: Characterization and Modeling _____ xxvii
Ran Cheng

Dominant Role of Air Ambient in Dynamic Bending Degradation of Flexible LTPS TFTs _____ xxviii
Mingxiang Wang

Design and process issues for high yield and reliability in thin BOX FD-SOI _____ xxix
Yoshiki Yamamoto

Multi-Functionalities and Applications of Dual-Port Ferroelectric FET _____ xxx
Kai Ni

Wurtzite-Structured Ferroelectric Materials Growth and Film Properties _____ xxxi
Yi Tong

Disturb-Free Operation Scheme and Application for Multilevel Cell Ferroelectric FETs NAND Array _____ xxxii
Xiao Yu

Nanoscale Air Channel Devices for Emerging IC Applications _____ xxxiii
Jinshun Bi

Domain-specific computing with non-volatile multi-terminal devices _____ xxxiv
Kelvin Fong Xuanyao

Energy-Efficient SRAM with Emerging Technologies _____ xxxv
Vita Pi-Ho Hu

Tutorials

RISC-V Is Inevitable _____ xxxvi
Sam Rogan, Yoshihito Kondo

Empowering CMOS-VLSI by MEMS Technology - An Example of High-Voltage Photovoltaic Chiplet Integration for Autonomous Micro Robotic Systems _____ xxxvii
Yoshio Mita

Artificial Synapses Enabled Neuromorphic Computing: From Blueprints to Reality _____ xxxviii

Chun Zhao

GaN Power Device Technology and monolithic integrated GaN power systems _____ xxxix
Wen Liu

On-chip transmission lines for silicon CMOS 6G: From basics to open questions _____ xl
Shuhei Amakawa

Terahertz Resonant-Tunneling Diodes _____ xli
Safumi Suzuki

Ferro-Electronics: From Memory to Computing _____ xlii
Kai Ni

Technical Sessions

Memristor Based Mixed-Accuracy Computation-In-Memory System_____ 1
Ze Wang; Ruihua Yu; Bin Gao

Beyond Integer Quantization: Approximate Arithmetic for Machine Learning Accelerators _____ 6
James S. Tandon

Challenges in Generating True Random Numbers Considering the Variety of Corners, Aging, and Intentional Attacks _____ 10
Javad Bahrami; Jean-Luc Danger; Mohammad Ebrahimabadi; Sylvain Guilley; Naghmeh Karimi

Development of Neuromorphic Locomotion Generator With Switching Gait by Light Stimulation for Microrobots_____ 16
Kosei Sekiyama; Isuke Okuma; Wataru Nakayama; Lyu Shuxin; Katsuyuki Morishita; Ken Saito

A Design of BNN Accelerator Using Gate-Level Pipelined Self-Synchronous Circuit_____ 20
Amartuvshin Bayasgalan; Makoto Ikeda

Reservoir Computing Utilizing Ferroelectric-Gate-Insulator FETs and Capacitors_____ 25
Shinichi Takagi; Kasidit Toprasertpong; Eishin Nako; Zeyu Wang; Rikuo Suzuki; Shin-Yi Min; Mitsuru Takenaka; Ryosho Nakane

First Demonstration of BEOL-Compatible Amorphous InGaZnOx Channel Antiferroelectric (Hf0.2Zr0.8O2)-Enhanced Floating Gate Memory _____ 29
Zijie Zheng; Jiawei Xie; Yiyuan Sun; Xiaolin Wang; Leming Jiao; Zuopu Zhou; Qiwen Kong; Yue Chen; Ying Xu; Xiao Gong;

Insight Into Effects of Introducing Ag−In−Zn−S Quantum Dots on Switching Characteristics of TiO2-Based Memristor_____ 34
Nan He; Haiming Qin; Feng Xu; Hao Zhang; Yang Sheng; Yi Tong

Realization of Artificial Neuron With Firing Saturation Based on Single Memristive Device _____ 37
Yu Wang; Yanzhong Zhang; Yanji Wang; Xinyue An; Miaocheng Zhang; Xinpeng Wang; Hao Zhang; Rongqing Xu; Yi Tong

Millimeter-Wave Dual-Frequency Transformer-Based Rectifier_____ 41
Yun Fang; Hao Gao

Low-Power MEMS-Based CMOS Transceivers _____ 44
Kai Tang; Ting Guo; Xiaolin Sun; Chun Zhao; Hao Gao; Yuanjin Zheng

A 60-GHz Transformer-Based Power Amplifier Supporting 5G n263-Band Applications_____ 48

Junqing Liu; Zheng Li; Minghao Fan; Yilun Chen; Atsushi Shirane; Kenichi Okada

Simulation and Analysis of Two GaN MIS-HEMT-Based Step-Down Level Shifters _____ 52
Junzhe Tan; Dongyi Yang; Shiqiang Wu; Yuhao Zhu; Yaoyao Pan; Pengju Cui; Wen Liu

A Monolithic Gallium Nitride Driver With Zero-Voltage-Switching and Dead Time Control _____ 57
Pingyu Cao; Yihua Wu; Yinchao Zhao; Miao Cui

39 - 67 GHz CMOS Multistage Power Amplifier With Two-Way Power Stage _____ 61
Sho Okii; Shinsuke Hara; Akifumi Kasamatsu; Yohtaro Umeda; Kyoya Takano

A High Resolution and Wide Range Temperature Detector Using 180-nm CMOS Process _____ 64
Ralph Gerard B. Sangalang; Shih-Heng Luo; Chua-Chin Wang

Frequency Dependency of Soft Error Rates Based on Dynamic Soft Error Measurements _____ 68
Haruto Sugisaki; Ryuichi Nakajima; Shotaro Sugitani; Jun Furuta; Kazutoshi Kobayashi

SEU Sensitivity of PMOS and NMOS Transistors in a 65 nm Bulk Process by α-Particle Irradiation _____ 72
Keita Yoshida; Ryuichi Nakajima; Shotaro Sugitani; Takafumi Ito; Jun Furuta; Kazutoshi Kobayashi

Dynamic Circuit Characterization and a Single Ring-Oscillator-Based Test Structure for Its Timing Parameter Extraction _____ 76
Haoming Zhang; Shuowei Li; Tetsuya Iizuka

Anomalous Wafer Map Detection and Localization Using Unsupervised Learning _____ 80
Lin Zhao; Chai Kiat Yeo

High-Frequency Operation of Low-Power Single-Flux-Quantum Circuits Fabricated Using 250 A/cm^2 Nb/AlO_x/Nb Planarization Process _____ 84
Masamitsu Tanaka; Yoshihiro Kitagawa; Tetsuro Satoh; Tsuyoshi Yamamoto

A 1-5GHz Inverter-Based Phase Interpolator With All Digital Control for Spin-Wave Detection Circuit _____ 88
Yuyang Zhu; Zunsong Yang; Zhenyu Cheng; Md Shamim Sarker; Hiroyasu Yamahara; Munetoshi Seki; Hitoshi Tabata; Tetsuya Iizuka

Design of 1-5 GHz Two-Stage Noise-Canceling Low-Noise Amplifier With Gm-Boosting Technique for Spin Wave Detection Circuit _____ 92
Zhenyu Cheng; Zunsong Yang; Yuyang Zhu; Md Shamim Sarker; Hiroyasu Yamahara; Munetoshi Seki; Hitoshi Tabata; Tetsuya Iizuka

Template-Based Design Optimization for Multiple Pairing-Friendly Curve Parameters _____ 96
Momoko Fukuda; Makoto Ikeda

High-Throughput Key Switching Accelerator for Homomorphic Encryption _____ 100
Zeyu Wang; Makoto Ikeda

Versatile Resource-Shared Cryptographic Accelerator for Multi-Domain Applications _____ 104
Vu Trung Duong Le; Hoai Luan Pham; Thi Hong Tran; Quoc Duy Nam Nguyen; Sang Duong Thi; Yasuhiko Nakashima

SibProMQTT: Protection of the MQTT Communication Protocol Against Sybil Attacks Applied for IoT Devices _____ 108
Favian Dewanta; Ida Wahidah; Sofia Naning Hertiana; Danu Dwi Sanjoyo; Sharifah Hafizah Syed Ariffin

Assessing the Vulnerability of Time-Controlled Logic-Loop-Based Circuits to Voltage Fault Injection and Power Monitoring Attacks ____ 112
Ye Ziyang; Makoto Ikeda

Investigation of Random Telegraph Noise in Advanced Silicon-On-Insulator N-FETs: The Impact of Back Bias, Strain, and Hot Carrier Stress ____ 116
Xinze Li; Yuxuan Wu; Qiao Teng; Yin Sun; Xiao Gong; Guillaume Besnard; Christophe Maleville; Olivier Weber; Rui Zhang; Bing Chen; Dawei Gao; Ran Cheng

Systematic Study on Predicting the Lifetime of Si pMOSFETs During NBTI Stress Based on Low-Frequency Noise ____ 120
Yi Jiang;Yanning Chen; Fang Liu; Bo Wu; Yongfeng Deng; Junkang Li; Dawei Gao; Rui Zhang

The Performance of FRAM Integrated With 3D Trench Hf0.5Zr0.5O2 Ferroelectric Capacitor __ 124
Jianjun Li; Tao Du; Wei Li

Effect of Mobile Ions on Subthreshold Swing of HfO2-Based Ferroelectric Field-Effect Transistors ____ 127
Jiajia Chen; Jiani Gu; Zhi Gong; Chengji Jin; Huan Liu; Xiao Yu; Genquan Han

Strategy for Improving Cycle of Maximized Energy Output of Triboelectric Nanogenerators ____ 131
Yirui Su; Masao Yanagisawa; Youhua Shi

Thin-Film Transistor-Based Tribotronic Artificial Synapse With Neurosensory Behavior _____ 136
H Lei; Y X Cao; C Zhao

Impact of Programming Process on Temperature Coefficient in Analog RRAM _____ 141
Siyao Yang; Bin Gao; Jianshi Tang; Feng Xu; Peng Yao; He Qian; Huaqiang Wu

A Study of Scattering Structures for High Sensitive Near-Infrared Pixels_____ 145
Godeun Seok; Yunkyung Kim

The Investigation of Source Field Plate on the Performance of pGaN Gate Device and Dual-Gate Bidirectional Switch Using TCAD Simulation_____ 148
Xuan Chi; Yubo Wang; Fan Li; Yixiao Huang; Chenruiyuan Yu; Shiqiang Wu; Huiqing Wen; Jiangmin Gu; Ping Zhang; Wen Liu

The Comparison of Dynamic Performance Between Hydrogen Treated and Etched pGaN HEMTs 152
Shiqiang Wu; Fan Li; Yuhao Zhu; Yixiao Huang; Chenruiyuan Yu; Yubo Wang; Xuan Chi; Huiqing Wen; Wen Liu

Physics-Based Small-Signal Model of Ga2O3 Hot-Electron Transistor _____ 156
Ruopu Zhu; Chengwei Liu; Yuhao Zhu; Wen Liu; Yi Pei; Man Hoi Wong

Electrical Properties of Each Channels in Vertical Stacked Gate-All-Around Nanosheet s-Si pMOSFETs ____ 159
Jing Yan; Junkang Li; Rui

Author Index ____ 163